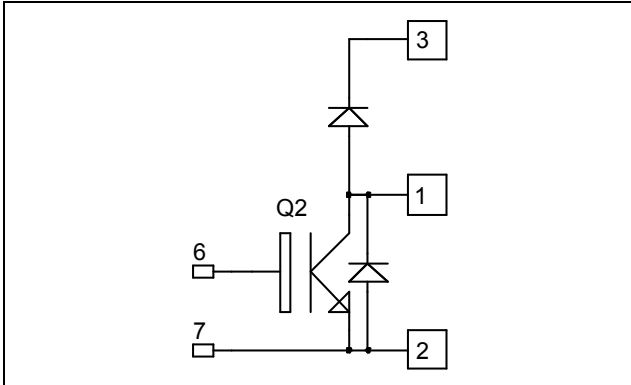


Boost chopper NPT IGBT Power Module

$V_{CES} = 600V$
 $I_C = 165A @ T_c = 80^\circ C$

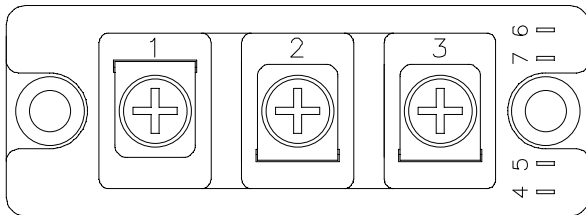


Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features

- Non Punch Through (NPT) FAST IGBT
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- High level of integration
- M5 power connectors



Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive T_C of V_{CEsat}
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	600	V
I_C	Continuous Collector Current	$T_C = 25^\circ C$	230
		$T_C = 80^\circ C$	165
I_{CM}	Pulsed Collector Current	$T_C = 25^\circ C$	400
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_C = 25^\circ C$	781
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	400A@420V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 600\text{V}$	$T_j = 25^\circ\text{C}$			250	μA
			$T_j = 125^\circ\text{C}$			500	
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 200\text{A}$	$T_j = 25^\circ\text{C}$		1.95	2.45	V
			$T_j = 125^\circ\text{C}$		2.2		
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 4\text{mA}$	4.5		6.5	V	
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20\text{V}, V_{CE} = 0\text{V}$			400	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}, V_{CE} = 25\text{V}$ $f = 1\text{MHz}$		9000		pF
C_{res}	Reverse Transfer Capacitance			800		
Q_G	Gate charge	$V_{GE} = 15\text{V}, I_C = 200\text{A}$ $V_{CE} = 300\text{V}$		650		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 200\text{A}$ $R_G = 16\Omega$		150		ns
T_r	Rise Time			72		
$T_{d(off)}$	Turn-off Delay Time			530		
T_f	Fall Time			40		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$ $I_C = 200\text{A}$ $R_G = 16\Omega$		160		ns
T_r	Rise Time			75		
$T_{d(off)}$	Turn-off Delay Time			550		
T_f	Fall Time			50		
E_{on}	Turn on energy	$V_{GE} = \pm 15\text{V}$ $V_{Bus} = 300\text{V}$	$T_j = 125^\circ\text{C}$	9		mJ
E_{off}	Turn off energy	$I_C = 200\text{A}$ $R_G = 16\Omega$		8.5		
I_{sc}	Short Circuit data	$V_{GE} \leq 15\text{V}; V_{Bus} = 360\text{V}$ $t_p \leq 10\mu\text{s}; T_j = 125^\circ\text{C}$		900		A

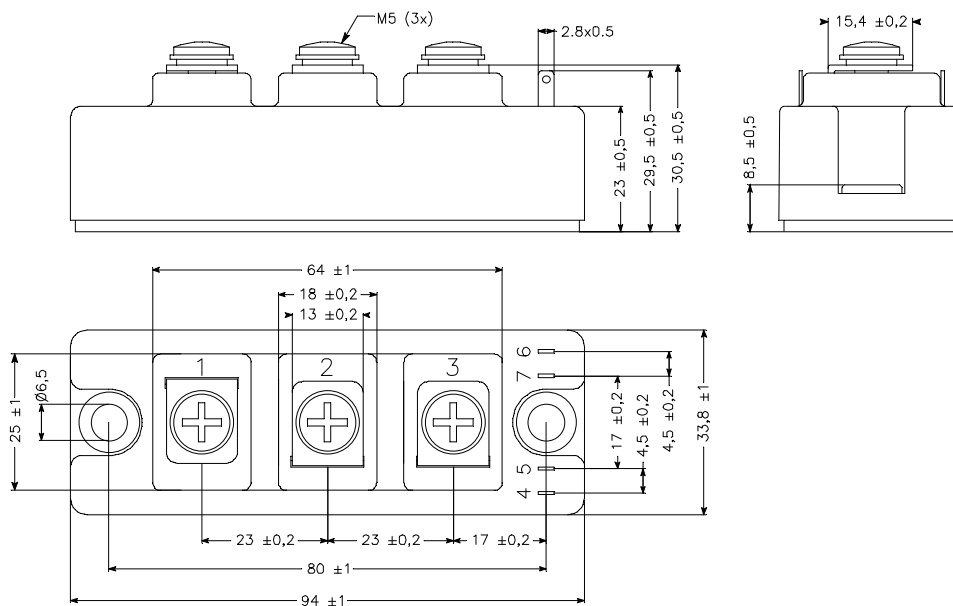
Chopper Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		600			V	
I_{RM}	Maximum Reverse Leakage Current	$V_R = 600\text{V}$	$T_j = 25^\circ\text{C}$		100	μA	
			$T_j = 125^\circ\text{C}$		500		
I_F	DC Forward Current			200		A	
V_F	Diode Forward Voltage	$I_F = 200\text{A}$ $V_{GE} = 0\text{V}$	$T_j = 25^\circ\text{C}$		1.25	1.6	V
			$T_j = 125^\circ\text{C}$		1.2		
t_{rr}	Reverse Recovery time	$I_F = 200\text{A}$ $V_R = 300\text{V}$ $di/dt = 3500\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		150	ns	
			$T_j = 125^\circ\text{C}$		250		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$		13	μC	
			$T_j = 125^\circ\text{C}$		20		
E_{rr}	Reverse Recovery Energy	$T_j = 25^\circ\text{C}$		2.9	mJ		
		$T_j = 125^\circ\text{C}$		5.7			

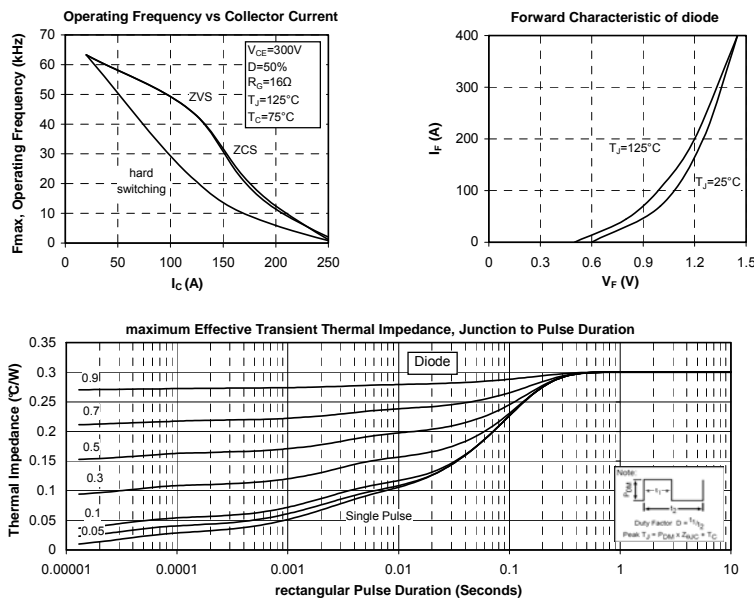
Thermal and package characteristics

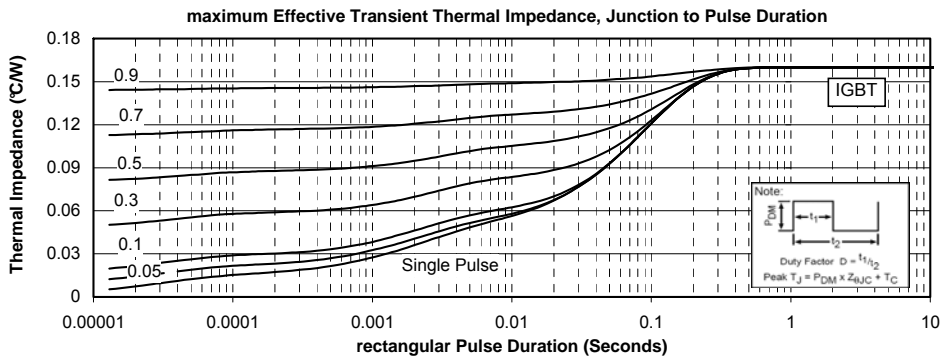
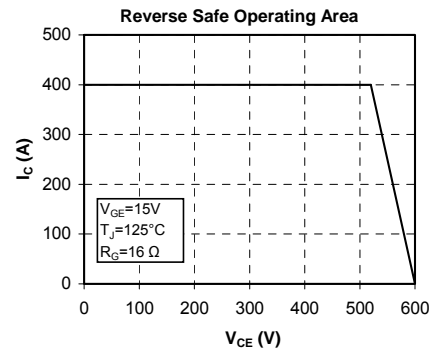
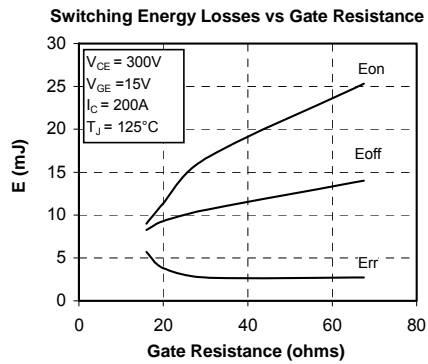
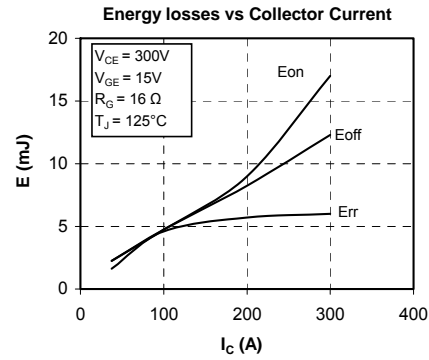
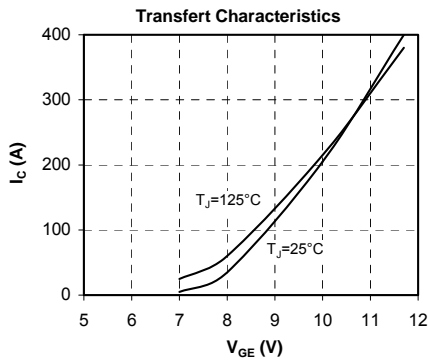
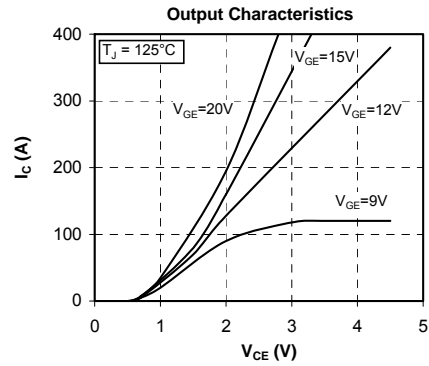
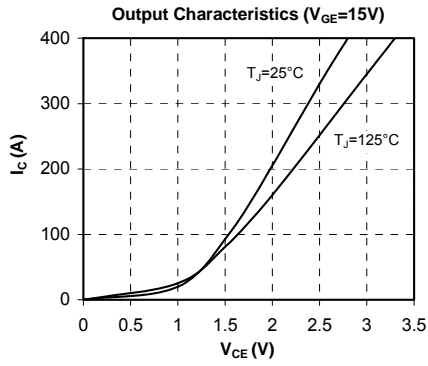
Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance	IGBT		0.16	°C/W	
		Diode		0.30		
V_{ISOL}	RMS Isolation Voltage, any terminal to case t=1 min, I isol<1mA, 50/60Hz	4000			V	
T_J	Operating junction temperature range	-40		150	°C	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		125		
Torque	Mounting torque	For terminals	M5	2	3.5	N.m
		To Heatsink	M6	3	5	
Wt	Package Weight			180	g	

D1 Package outline (dimensions in mm)



Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 6,939,743 7,352,045 5,283,201 5,801,417 5,648,283 7,196,634 6,664,594 7,157,886 6,939,743 7,342,262 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.